

## CLAIMS

- [1] A two-beam semiconductor laser device comprising:
- a two-beam semiconductor element having a first and a second semiconductor laser elements that can be driven independently and that are formed integrally on a substrate; and
  - a submount having, mounted on a front part thereof, the two-beam semiconductor laser element with a light-emitting face thereof directed forward and having a first and a second electrode pads connected to electrodes of the first and second semiconductor laser element by being kept in contact therewith,
  - wherein the first and second electrode pads are formed to extend farther behind the two-beam semiconductor laser element, and are wire-bonded behind the two-beam semiconductor laser element.
- [2] The two-beam semiconductor laser device of claim 1,
- wherein the first and second electrode pads are wire-bonded at a rear end of the submount.
- [3] The two-beam semiconductor laser device of claim 1 or 2,
- wherein a distance from the rear end of the two-beam semiconductor laser element to a position where the first and second electrode pads are wire-bonded is 300  $\mu\text{m}$  or shorter.
- [4] The two-beam semiconductor laser device of one of claims 1 to 3,
- wherein a lateral length of the submount is 400  $\mu\text{m}$  or more but 700  $\mu\text{m}$  or less.
- [5] The two-beam semiconductor laser device of one of claims 1 to 4,

wherein the submount is mounted in a package composed of a frame and a resin member.

[6] The two-beam semiconductor laser device of claim 5,

wherein the two-beam semiconductor laser device is built as a three-terminal two-beam semiconductor laser device having three terminals.